

ABSTRACT

METHOD AND STRUCTURE FOR A SELF-ALIGNED SILICIDED WORD LINE AND POLYSILICON PLUG DURING THE FORMATION OF A SEMICONDUCTOR DEVICE

A method used to form a semiconductor device provides a silicide layer on a plurality of transistor word lines and on a plurality of conductive plugs. In one embodiment, the word lines, one or more sacrificial dielectric layers on the word lines, conductive plugs, and a conductive enhancement layer are formed through the use of a single mask. An in-process semiconductor device which can be formed using one embodiment of the inventive method is also described.